



# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

The is Designed for

## FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

<b>I<sub>C</sub></b>	43.2 A
<b>V<sub>CB0</sub></b>	65 V
<b>V<sub>CES</sub></b>	65 V
<b>V<sub>EBO</sub></b>	3.5 V
<b>P<sub>DISS</sub></b>	1167 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	0.15 °C/W

**PACKAGE STYLE .400 BAL FLG(A)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.210 / 5.33	.230 / 5.84
B	.045 / 1.14	.055 / 1.40
C	.125 / 3.18	.135 / 3.43
D	.380 / 9.65	.390 / 9.91
E	.770 / 19.56	.830 / 21.08
F	.070 / 1.78	.080 / 2.03
G	.215 / 5.46	.235 / 5.97
H	.420 / 10.67	.430 / 10.92
I	.645 / 16.38	.655 / 16.64
J	.895 / 22.73	.905 / 22.99
K	.002 / 0.05	.006 / 0.15
L	.058 / 1.47	.065 / 1.65
M	.115 / 2.92	.130 / 3.30
N		.230 / 5.84
P	.395 / 10.03	.405 / 10.29

**ORDER CODE: ASI10687**

## CHARACTERISTICS T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 50 mA			65			<b>V</b>
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 50 mA			65			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA			3.5			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 30 V					15	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V	I <sub>C</sub> = 5.0 A		20		200	<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CE</sub> = 40 V	P <sub>IN</sub> = 54 W	f = 425 MHz	9.7			<b>dB</b>
<b>η<sub>C</sub></b>				50			<b>%</b>